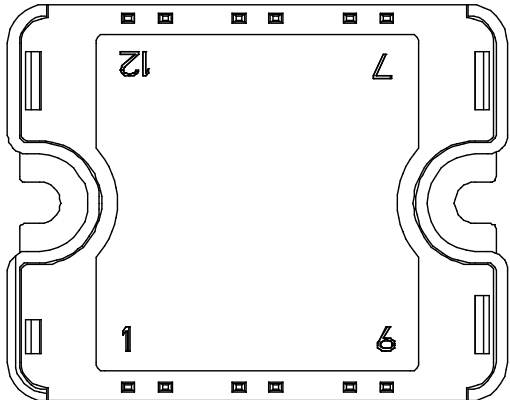
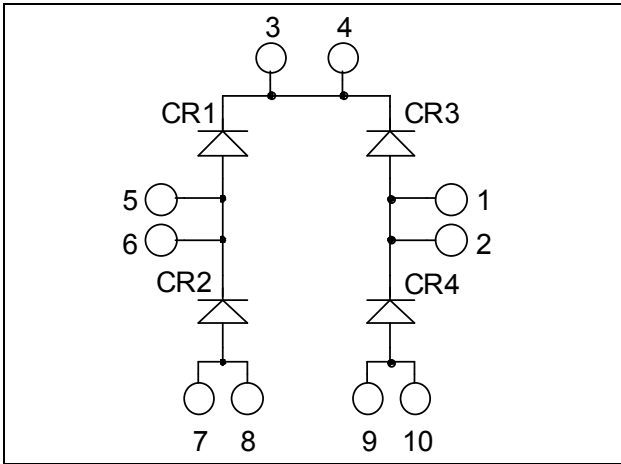


Fast Diode Full Bridge Power Module

$V_{RRM} = 1200V$
 $I_C = 100A @ T_c = 60^\circ C$



All multiple inputs and outputs must be shorted together
 3/4 ; 5/6 ; 7/8 ; 1/2 ; 9/10

Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
V_R	Maximum DC reverse Voltage	1200	V	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	$T_C = 25^\circ C$	A
			$T_C = 60^\circ C$	
I_{FSM}	Non-Repetitive Forward Surge Current	8.3ms	$T_C = 45^\circ C$	500

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_F	Diode Forward Voltage	$I_F = 100\text{A}$			2.4	3	V
		$I_F = 150\text{A}$			2.7		
		$I_F = 100\text{A}$	$T_j = 125^\circ\text{C}$		1.8		
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
C_T	Junction Capacitance	$V_R = 200\text{V}$			110		pF

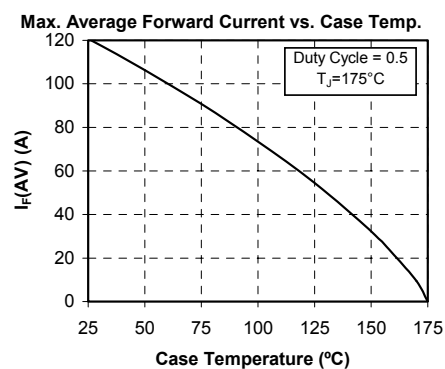
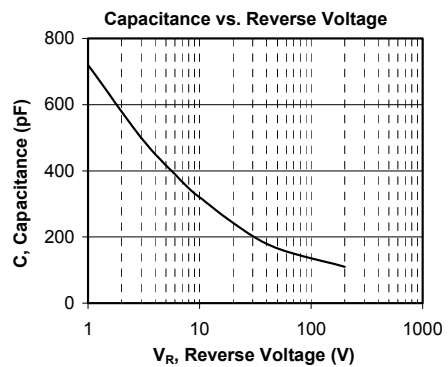
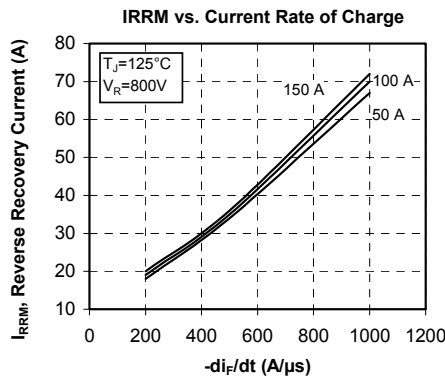
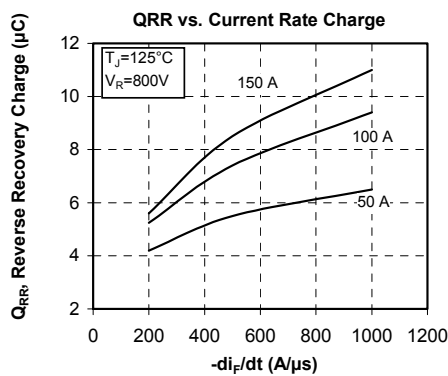
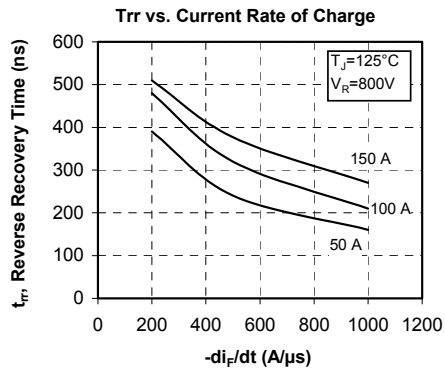
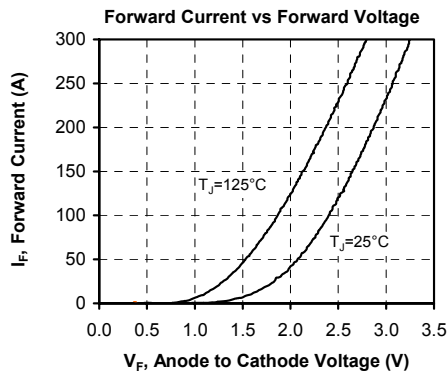
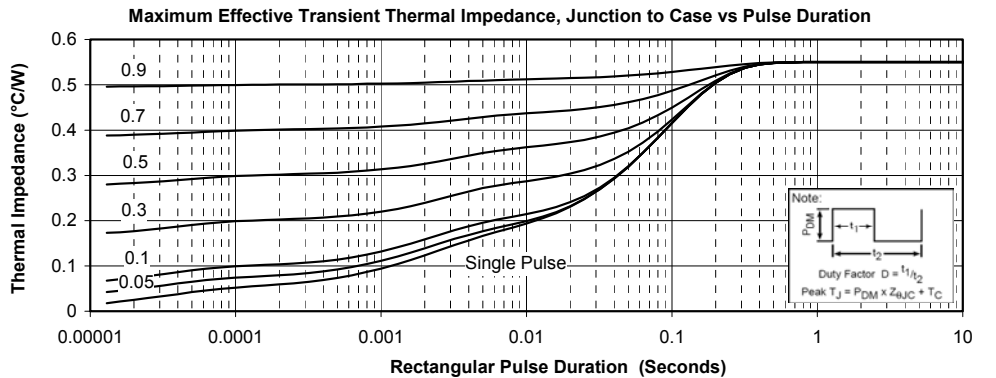
Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$	$T_j = 25^\circ\text{C}$		385		ns
			$T_j = 125^\circ\text{C}$		480		
Q_{rr}	Reverse Recovery Charge	$V_R = 800\text{V}$	$di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		1055	nC
				$T_j = 125^\circ\text{C}$		5240	
I_{RRM}	Reverse Recovery Current	$V_R = 800\text{V}$	$di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		6	A
				$T_j = 125^\circ\text{C}$		19	
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$	$V_R = 800\text{V}$	$T_j = 125^\circ\text{C}$		210	ns
Q_{rr}	Reverse Recovery Charge					9.4	μC
I_{RRM}	Reverse Recovery Current					70	A

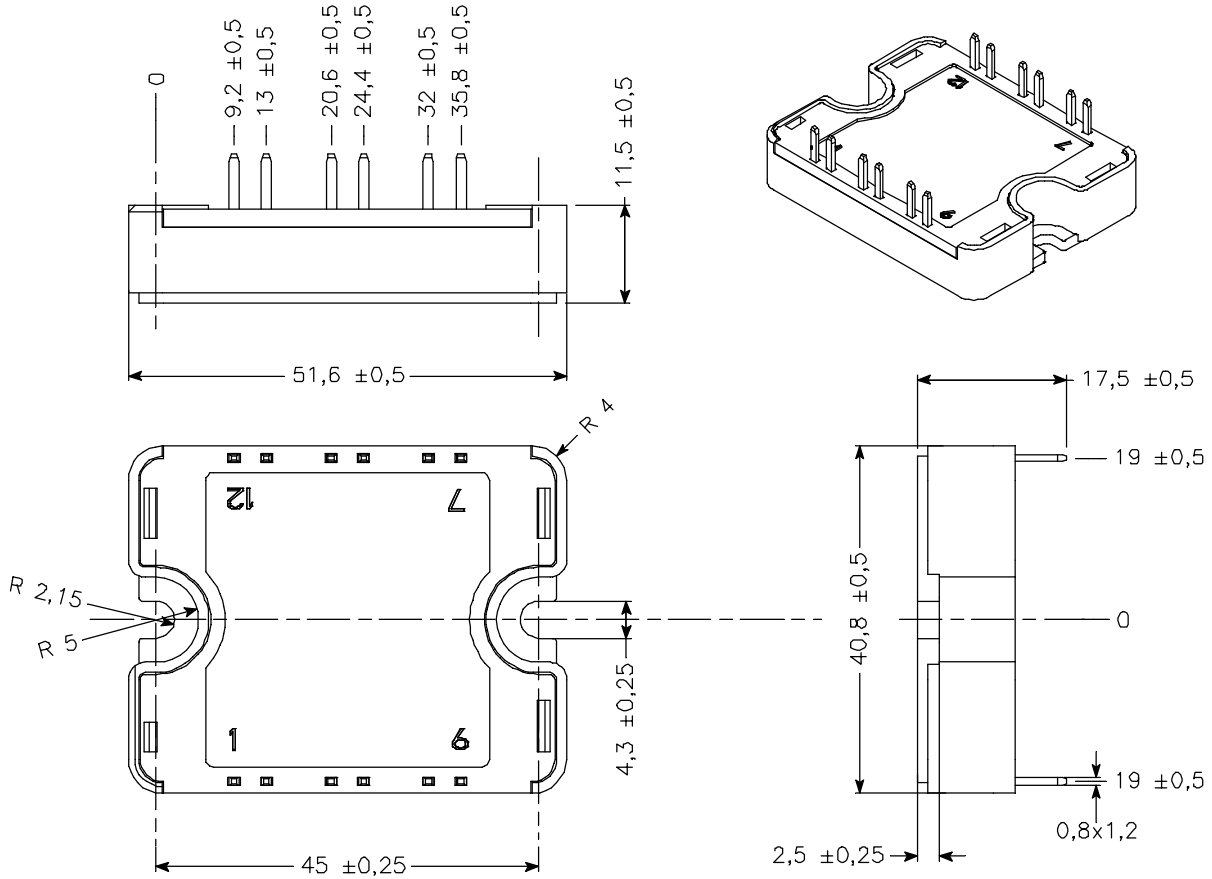
Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance			0.55	$^\circ\text{C}/\text{W}$	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$, $I_{isol} < 1\text{mA}$, 50/60Hz	2500			V	
T_J	Operating junction temperature range	-40		175	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

Typical Performance Curve



SP1 Package outline (dimensions in mm)



See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.